| L Number | Hits | Search Text | DB | Time stamp |
|---|---|---|---|---|
| - | 2 | (("6258220") or ("6508920")).PN. | USPAT | 2004/09/09 15:06 |
| - | 2 | ((("6258220") or ("6508920")).PN.) and wafer | USPAT | 2004/08/31 08:56 |
| - | 2 | ((("6258220") or ("6508920")).PN.) and wafer and anneal$4 | USPAT | 2004/08/31 08:56 |
| - | 2 | ((("6258220") or ("6508920")).PN.) and wafer and (first with second) and anneal$4 | USPAT | 2004/08/31 08:57 |
| - | 2 | ((("6258220") or ("6508920")).PN.) and wafer and (first with second) and anneal$4 and cool | USPAT | 2004/08/31 08:57 |
| - | 0 | ((("6258220") or ("6508920")).PN.) and wafer and (first with second) and anneal$4 and cool and hour | USPAT | 2004/08/31 08:57 |
| - | 2 | ((("6258220") or ("6508920")).PN.) and wafer and (first with second) and anneal$4 and cool and time | USPAT | 2004/08/31 08:57 |
| - | 2 | ((("6258220") or ("6508920")).PN.) and wafer and (first with second) and anneal$4 and cool and time and temperature | USPAT | 2004/08/31 09:06 |
| - | 527 | 438/758.ccls. | USPAT | 2004/08/31 09:06 |
| - | 38 | 438/758.ccls. and (wafer with anneal$4) | USPAT | 2004/08/31 09:07 |
| - | 16 | 438/758.ccls. and (wafer with anneal$4) and (first with second) and anneal | USPAT | 2004/08/31 09:07 |
| - | 16 | 438/758.ccls. and (wafer with anneal$4) and (first with second) and anneal and temperature | USPAT | 2004/08/31 09:07 |
| - | 6 | 438/758.ccls. and (wafer with anneal$4) and (first with second) and anneal and temperature and cool$4 | USPAT | 2004/09/02 08:23 |
| - | 6 | 438/758.ccls. and (wafer with anneal$4) and (first with second) and anneal and temperature and cool$4 and time | USPAT | 2004/08/31 10:49 |
| - | 596 | 438/660.ccls. | USPAT | 2004/08/31 10:50 |
| - | 82 | 438/660.ccls. and wafer and (first with second and anneal) | USPAT | 2004/08/31 10:50 |
| - | 80 | 438/660.ccls. and wafer and (first with second and anneal) and temperature | USPAT | 2004/08/31 10:50 |
| - | 77 | 438/660.ccls. and wafer and (first with second and anneal) and temperature and time | USPAT | 2004/08/31 10:50 |
| - | 61 | 438/660.ccls. and wafer and (first with second and anneal) and temperature and time and low | USPAT | 2004/08/31 10:50 |
| - | 20 | 438/660.ccls. and wafer and (first with second and anneal) and temperature and time and low and "400" | USPAT | 2004/08/31 10:51 |
| - | 0 | 438/660.ccls. and wafer and (first with second and anneal) and temperature and time and low and "0-400" | USPAT | 2004/08/31 10:52 |
| - | 40 | 438/660.ccls. and wafer and (first with second and anneal) and temperature and time and low and "200" | USPAT | 2004/08/31 10:52 |
| - | 24 | 438/660.ccls. and wafer and (first with second and anneal) and temperature and time and low and "300" | USPAT | 2004/08/31 10:53 |
| - | 6 | 438/660.ccls. and wafer and (first with second and anneal) and temperature and time and low and "300" and stress and copper | USPAT | 2004/08/31 10:53 |
| - | 20 | 438/795.ccls. and (wafer with anneal$4) and (first with second) and anneal and temperature and cool$4 | USPAT | 2004/09/02 08:24 |

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| - | 19321 | wafer and (first with second and anneal$4) | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/09/09 15:08 |
|---|---|---|---|---|
| - | 7189 | wafer and (first with second and anneal$4) and (low with temperature) | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/09/09 15:08 |
| - | 3267 | wafer and (first with second and anneal$4) and (low with temperature) and "400" | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/09/09 15:09 |
| - | 2008 | wafer and (first with second and anneal$4) and (low with temperature) and "400" and treat$4 | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/09/09 15:09 |
| - | 135 | wafer and (first with second and anneal$4) and (low with temperature) and "400" and treat$4 and microstructure | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/09/09 15:09 |
| - | 66 | wafer and (first with second and anneal$4) and (low with temperature) and "400" and treat$4 and microstructure and stress | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/09/09 15:10 |
| - | 15 | wafer and (first with second and anneal$4) and (low with temperature) and "400" and treat$4 and microstructure and stress and migration | USPAT; US-PGPUB; EPO; JPO; DERWENT | 2004/09/09 15:10 |